IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of: Robert J. Small Confirmation No. 9378

U.S. Patent No.: 6,777,380 Application No. 09/903,064

pplication No. 09/903,064 Art Unit: 1751

Issued : August 17, 2004 Filed: July 10, 2001

July 10, 2001 Examiner: Gregory E. Webb

For: METHOD OF CHEMICALLY

MECHANICALLY POLISHING SUBSTRATES

U.S. Patent and Trademark Office Randolph Building 401 Dulaney Street Alexandria, Virginia 22314

Sir:

SUBMISSION OF REVOCATION OF ORIGINAL POWER OF ATTORNEY AND GRANT OF NEW POWER OF ATTORNEY

Enclosed is a copy of the Revocation of Original Power of Attorney and Grant of New Power of Attorney by the Assignee, EKC Technology, Inc. Assignee directs the Patent and Trademark Office to send all future correspondence to:

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If there is any fee due in connection with the filing of this Submission, please charge the fee to Morgan, Lewis & Bockius LLP Deposit Account No. 50-0310.

By:

Respectfully submitted,

January 28 2009

Victor N. Balancia Reg. No. 31,231

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Washington, D.C. 20004

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REVOCATION AND POWER OF ATTORNEY

Commissioner for Patents P. O. Box 1450 Alexandria, Virginia 22313-1450

Sir:

EKC Technology, Inc., owner of the entire right, title and interest in, to and under the inventions described and claimed in the patent applications identified in the attached Schedule A, hereby revokes all previous powers of attorney and appoints Morgan, Lewis & Bockius LLP, Customer Number 009629, and each of them, its attorneys, to prosecute each of these patent applications, and to transact all business in the Patent and Trademark Office connected therewith.

Please direct all future correspondence to Customer No. 009629, Patent Support Unit, Morgan, Lewis & Bockius LP, 1111 Pennsylvania Avenue, N.W., Washington, D.C. 20004, and direct all telephone calls to Morgan, Lewis & Bockius LLP at 202-739-3000.

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Signature:

Typed Name Michael A. Fury

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Oxalic Acid as a Semiaqueous Cleaning Product for Copper and Dielectrics Lee, et al. 04/24/2003 60937-116-US 8317-116-US	Schedule A					
and Plasma Etched Residues for Semiconductor Devices Small, et al. 07/10/2001 60937-091-US 8317-091-US 09/874,330 Substrate Pre-Treatment Maloney, et al. 06/06/2001 60937-111-US 8317-111-US	App 4.8	TO SECURITION OF THE PARTY OF T	fayentoris) a S		New Allomey Dockel No.	Former Attorney
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Chemical Mechanical Polishing Compositions Small, et al. 11/06/2001 60937-114-US 8317-114-US 8317-116-US 8317-116-US 8317-116-US 8317-116-US 8317-116-US 8317-118-US 8317-120-US 8317-120-US 8317-120-US 8317-120-US 8317-120-US 8317-123-US 8317-12	09/874,330		Maloney, et al.	06/06/2001	60937-111-US	8317-111-999
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Cleaning Solutions Including Nucleophilic Amine Compound Having Reduction and Oxidation 09/988,545 Potential Lee, et al. 11/20/2001 60937-127-US 8317-127-9 Method and Compositions for Chemically Treating A Substrate 10/060,109 Using Foam Technology Patel, et al. 01/28/2002 60937-129-US 8317-129-9						
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Having Reduction and Oxidation 11/20/2001 60937-127-US 8317-127-5						
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	10/060,109		Patel, et al.	01/28/2002	60937-129-US	8317-129-999
Cleaning Solution Including			•			:
Nucleophilic Amine Compound	•		· · · · · · · · · · · · · · · · · · ·			: :
Having Reduction and Oxidation	40/405 005	•		05/04/0000		
						8317-135-999
	10/446,127		Melvin K, Carter	05/30/2003	60937-137-05	8317-137-999
Process for the Use of Bis-Choline and Tris-Choline in the Cleaning of						
Quartz-Coated Polysilicon and Other			,		,	
	10/689 657		Charm et al	10/22/2003	60937-139-115	8317-139-999
. Cleaning Compositions Containing			<u> </u>		00007 100 00	100 000
Hydroxylamine Derivatives and	,					
Process Using Same for Residue		Process Using Same for Residue				
10/689,620 Removal Zhou, et al. 10/22/2003 60937-140-US 8317-140-9	10/689,620	Removal	Zhou, et al.	10/22/2003	60937-140-US	8317-140-999
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Composition for Exfoliation Agent to	10/000 040		1	40000000	ا در ده ده ده ده	
	10/089,616		Melvin K. Carter	10/22/2003	60937-141-US	8317-141-999
Reducing Oxide Loss When Using Fluonde Chemistries to Remove Post-			·	·		
Etch Residues in Semiconductor				٠. ا		•
	60/467.131		Lee, et al.	05/02/2003	60937-142-PR	8317-142-888

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		anventors)	Dale	A CONTRACTOR OF THE PART OF TH	Dockel No.
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10/630,301	Films of Materials	Hill, et al.	·07/30/2003	60937-143-US	8317-143-999
10/030,001	Methods for the Deposition of Silver				•
	and Silver Oxide Films and Patterned				
10/716,838	Films	Ruan, et al.	11/18/2003	60937-147-US	8317-147-999
10/1 10,000	Semiconductor Process Residue				
10/162,679	Removal Composition and Process	Lee, et al.	06/06/2002	60937-149-US	8317-149-999
10,102,070	System and Method for Cleaning				
0	Workpieces Using Supercritical				' .
60/469,826	Carbon Dioxide	Fury, et al.	05/13/2003	60937-150-PR	8317-150-888
				,	
	Abrasive-Free Chemical Mechanical	•			
	Polishing Composition and Polishing			•	
10/689,043	Process Containing Same	Yao, et al.	10/21/2003	60937-151-US	8317-151-999
	,				
10/689,042	Wet Etch of Titanium-Tungsten Film	Patel, et al.	10/21/2003	60937-152-US	8317-152-999
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	Method of Depositing Nanostructured			22227 452 112	0047 450 000
10/261,197	Films with Embedded Nanopores	Svendsen, et al.	09/30/2002	60937-153-US	8317-153-999
·	Hydrothermal Treatment of		40,000,000	20007 407 110	0247 467 000
10/280,270	Nanostructured Films	Mukherjee, et al.	10/23/2002	60937-167-US	8317-167-999
10/257,469	Inhibition of Titanium Corrosion	Daviot, et al.	10/11/2002	60937-168-US	8317-168-999
	Chemical Mechanical Polishing	Omenii al al	02/07/0002	60937-171-US	8317-171-999
10/401,405	Composition and Process	Small, et al.	03/27/2003	60937-171-03	0317-171-999
	Aqueous Phosphoric Acid				
	Compositions for Cleaning	Douglas as al	10/21/2003	60937-172-US	8317-172-999
10/688,900	Semiconductor Devices	Daviot, et al.	10/21/2003	00937-172-03	6311-172-635
	Load Lock System for Supercritical	Fury, et al.	06/18/2003	60937-175-US	8317-175-999
10/465,906	Fluid Cleaning Automated Dense Phase Fluid	ruiy, et al.	, 00/10/2003	00007-170-00	
	Cleaning System	Fury, et al.	06/18/2003	60937-176-US	8317-176-999
10/465,905	Residue Removers for	t.ury, et al.	00/10/2000	00001 110 00	
	Electrohydrodynamic Cleaning of				
60/455,439	Semiconductors	Robert J. Small	03/18/2003	60937-178-PR	8317-178-888
204,004100	Free Radical-Forming Activator				
	Attached to Solid and Used to				
10/264 022	Enhance CMP Formulations	Scott, et al.	02/11/2003	60937-179-US	8317-179-999
10/361,822	Titanium Carboxylate Films for Use in	Court or as			
10/377,533	Semiconductor Processing	Hill, et al.	02/26/2003	60937-182-US	8317-182-999
10/377,535	Method of Making Barrier Layers	Maloney, et al.	05/20/2003	60937-183-US	8317-183-999
10/422,000	Remover Formulation Containing				
	Fluoride for Use During	•			
60/463,739	Şemiconductor Manufacturing	Hirasawa, et al.	04/18/2003	60937-185-PR	8317-185-888
	Cleaning Composition for Removing				
	Resists and Manufacturing Method of	· •.			
60/4 64 ,125	Semiconductor Devices	Hirasawa, et al.	04/21/2003	60937-186-PR	8317-186-888
	Deposition of Permanent Polymer			1	
10/422,212	Structures for OLED Fabrication	Roman, et al.	04/23/2003	60937-187-US	8317-187-999
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10/442,858	Removal Composition and Process	Wai Mun Lee	05/20/2003	60937-189-US	8317-189-999
10/442,000	Cleaning Compositions and Method of	1	03/20/2003		0017-103-333
10/630,300	Use Thereof	Wai Mun Lee	07/30/2003	60937-194-US	8317-194-999
10/030,300	Compositions and Methods for	TY AI THUIT LOO	0170012000	00007 104 00	0011 104 000 1
	Rapidly Removing Overfilled		*		•
60/518,337	Substrates	Chelle, et al.	11/10/2003	60937-200-PR	8317-200-888
00/010,001	CMP Method for Copper, Tungsten,	<u> </u>		0000. 200. 1	
	Titanium, Polysilicon, and Other	·			
	Substrates Using Organosulfonic				
10/690,623	Acids as Oxidizers	Carter, et al.	10/23/2003	60937-202-US	8317-202-999
10/000/020	PeriodicAcid Compositions for			•	
	Polishing Nobel Metal/High K	• •			
60/494,954	Substrates	Robert J. Small	08/14/2003	60937-203-PR	8317-203-888
	Cerium Oxide Abrasives for Chemical				
60/509,920	Mechanical Polishing	Robert J. Small	10/10/2003	60937-204-PR	8317-204-888
	·			•	
•	Chemical Mechanical Polishing				
	Slurries and Cleaners Containing				
60/516,736	Salicyclic Acid as a Corrosion Inhibitor	Carter, et al.	11/04/2003	60937-206-PR	8317-206-888
	Periodic Acid Compositions for			•	χ.
60/494,955	Polishing Ruthenium Substrates	Robert J. Small	08/14/2003	60937-207-PR	8317-207-888
	Chemical Mechanical Polishing				
10/683,730	Compositions and Process	Small, et al.	10/10/2003	60937-211-US	8317-211-999
	Alumia Abrasive for Chemical		4040=4400		
60/514,020	Mechanical Polishing	Philippe H. Chelle	10/27/1999	60937-213-PR	8317-213-888
		•	•		•
	Chemical Mechanical Polishing				
50/500 054	Slurries and Cleaners Containing	Tamilmoni et el	09/16/2003	60937-214-PR	8317-214-888
60/502,951	Salicyclic Acid as a Corrosion Inhibitor Compositions for Chemical	Tamilmani, et al.	09/10/2003	00837-214-F.K	0317-214-000
	Mechanical Planarization of Tantalum	•			
10/665,417	and Tantalum Nitride	Small, et al.	09/22/2003	60937-215-US	8317-215-999
10/000,417	Alumina Abrasive for Chemical	Orrigin, Ct Gt.	33/22/2003	00001-210-00	JU11-210-000
60/526,107	Mechanical Polishing	Chelle, et al.	12/02/2003	60937-216-PR	8317-216-888
30/020,107	Particulate or Particle-Bound				
60/509,922	Chelating Agents	Small, et al.	10/10/2003	60937-217-PR	8317-217-888
30.000,022	Particulate or Particle-Bound				
10/690,626	Chelating Agents	Small, et al.	10/23/2003	60937-217-US	8317-217-999
	Chemical Mechanical Polishing of STI				
	Features on Semiconductors: Water	٠ _ ا	-	•	.
60/533,054	Polishing with Ceria Slurries	Yu, et al	12/30/2003	60937-223-PR	8317-223-888
	Removal of Post Etch Residues and		·	·	
·	Copper Contamination From Low-K				
	Dielectrics Using Superciritcal CO2		.		
60/511,949	with Diketone Additives	Jerome Daviot	_10/14/2003	60937-225-PR	8317-225-888
	Method and Apparatus for Substrate	, ,			:
10/694,999	Pre-Treatment	Lee, et al.	10/29/2003	60937-226-US	8317-226-999

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	Method of Chemically Mechanically					
60/515,450	Polishing Substrates	Brandon S. Scott	10/30/2003	60937-228-PR	8317-228-888	